

MBT2222ADW1, NSVBT2222ADW1

General Purpose Transistor

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	75	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	600	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1), $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

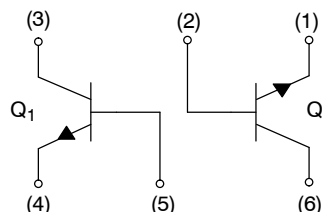
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



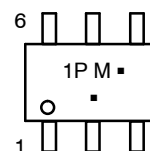
ON Semiconductor®

<http://onsemi.com>



SC-88/SC70-6/SOT-363
CASE 419B
STYLE 1

MARKING DIAGRAM



1P = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NSVBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	40	–	Vdc
Collector–Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	75	–	Vdc
Emitter–Base Breakdown Voltage, (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	–	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	I _{CEX}	–	10	nAdc
Collector Cutoff Current (V _{CB} = 60 Vdc, I _E = 0) (V _{CB} = 60 Vdc, I _E = 0, T _A = 125°C)	I _{CBO}	– –	0.01 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	I _{EBO}	–	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	I _{BL}	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = 0.1 mAdc, V _{CE} = 10 Vdc) (I _C = 1.0 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc, T _A = –55°C) (I _C = 150 mAdc, V _{CE} = 10 Vdc) (Note 2) (I _C = 150 mAdc, V _{CE} = 1.0 Vdc) (Note 2) (I _C = 500 mAdc, V _{CE} = 10 Vdc) (Note 2)	h _{FE}	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector–Emitter Saturation Voltage (Note 2) (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	V _{CE(sat)}	– –	0.3 1.0	Vdc
Base–Emitter Saturation Voltage (Note 2) (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	V _{BE(sat)}	0.6 –	1.2 2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 3) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	–	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	–	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	–	25	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{re}	– –	8.0 4.0	X 10 ^{–4}
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	50 75	300 375	–
Output Admittance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8 MHz)	rb, C _C	–	150	ps
Noise Figure (I _C = 100 μAdc, V _{CE} = 10 Vdc, R _S = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 30 Vdc, V _{BE(off)} = –0.5 Vdc, I _C = 150 mAdc, I _{B1} = 15 mAdc)	t _d	–	10	ns
Rise Time		t _r	–	25	
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc, I _{B1} = I _{B2} = 15 mAdc)	t _s	–	225	ns
Fall Time		t _f	–	60	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

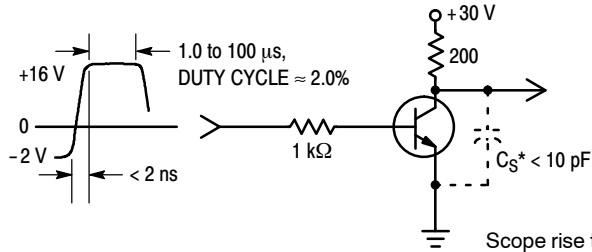


Figure 1. Turn-On Time

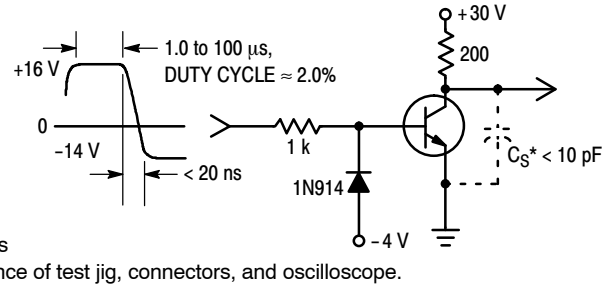


Figure 2. Turn-Off Time

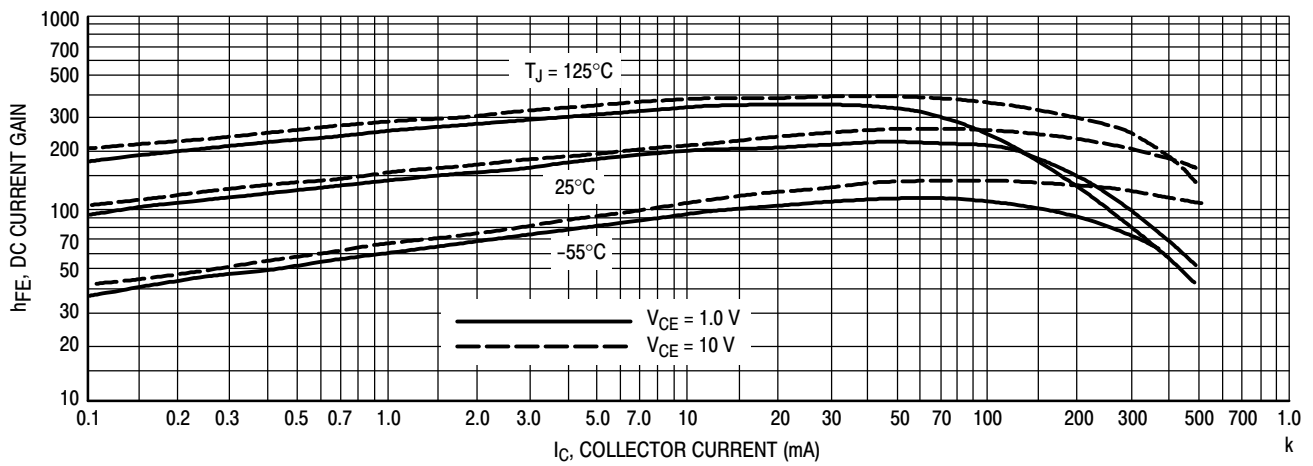


Figure 3. DC Current Gain

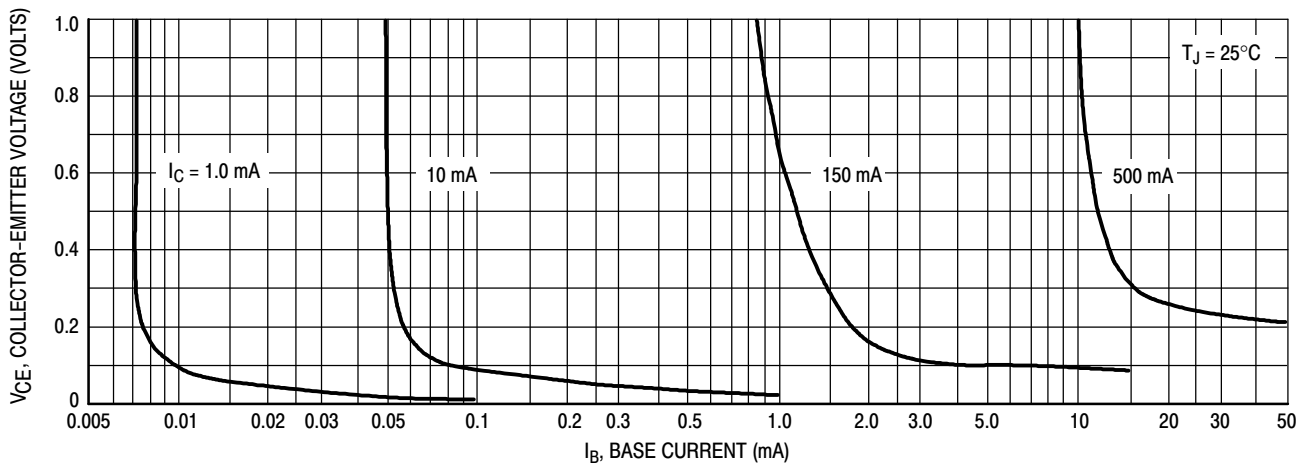


Figure 4. Collector Saturation Region

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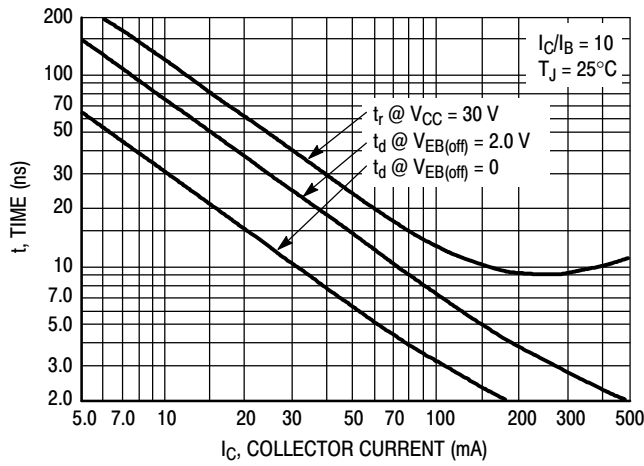


Figure 5. Turn-On Time

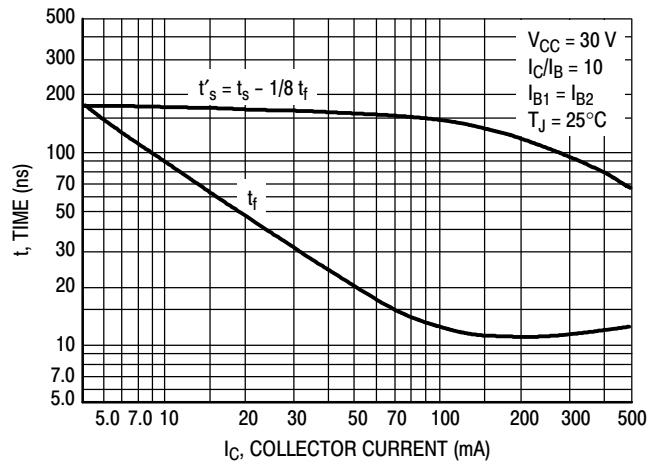


Figure 6. Turn-Off Time

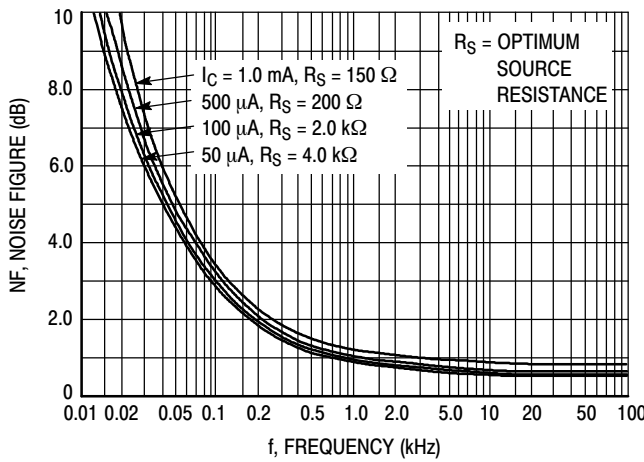


Figure 7. Frequency Effects

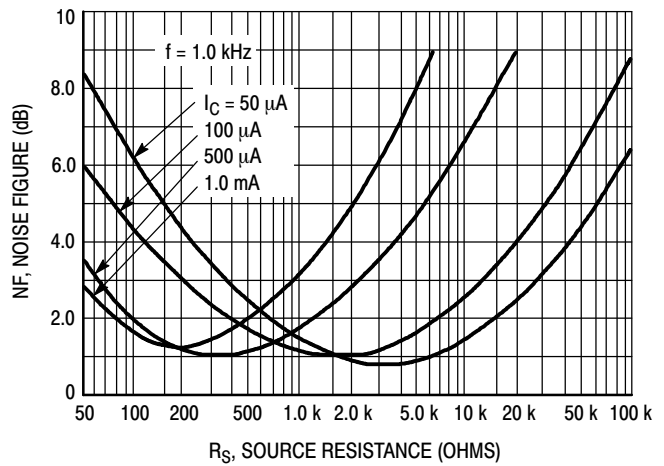


Figure 8. Source Resistance Effects

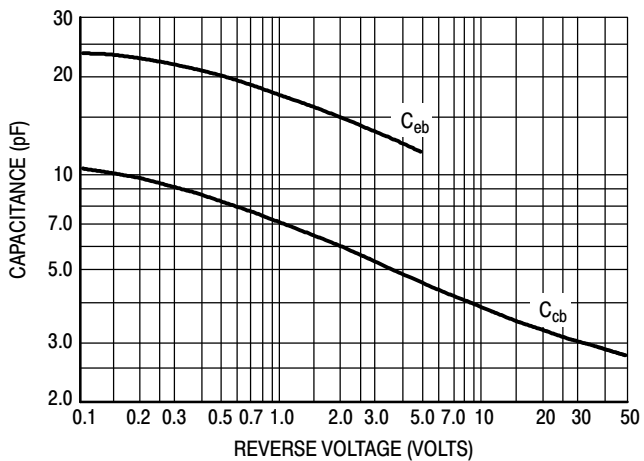


Figure 9. Capacitances

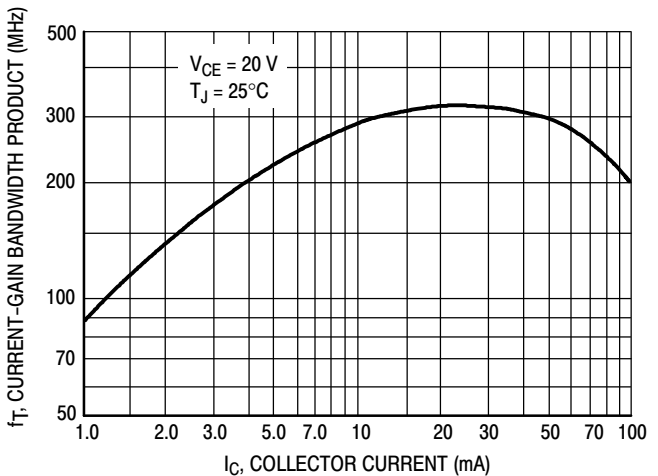


Figure 10. Current-Gain Bandwidth Product

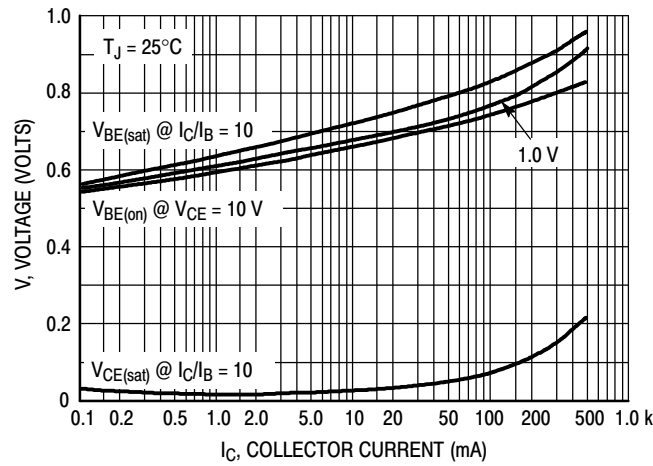


Figure 11. "On" Voltages

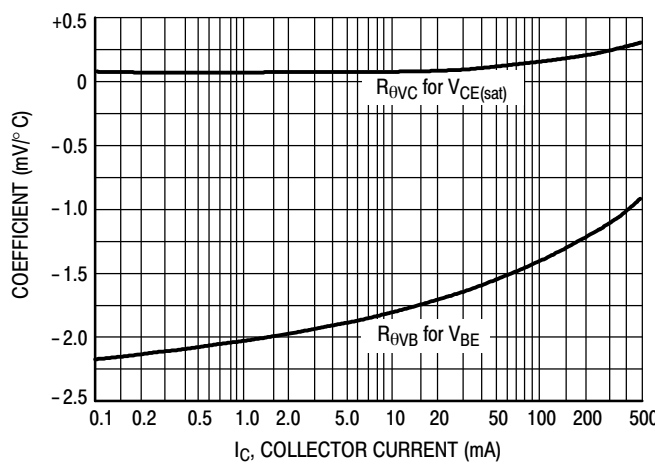


Figure 12. Temperature Coefficients

